



GAU 9824
#4 /666 art
5/26/00
PATENT
81788.0025
18

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Seiichi Mori

Serial No: 09/451,619

Filed: November 30, 1999

For: NON-VOLATILE
SEMICONDUCTOR MEMORY AND
MANUFACTURING METHOD
THEREOF

Art Unit: 2824

Examiner: Not Assigned

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to:

Assistant Commissioner for Patents
Washington D.C. 20231, on

May 2, 2000

Date of Deposit

William H. Wright

Name

May 2, 2000

Signature

Date

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

The information disclosure statement submitted herewith is being filed before a first action on the merits for the subject application and contains no items of information cited in any communication from a foreign patent office in a counterpart foreign application [37 C.F.R. § 1.97(e)(1)].

If it should be determined that for any reason either an insufficient or excessive fee has been paid, please charge any insufficiency or credit any overpayment necessary to ensure consideration of the information disclosure statement for the above-identified application to Deposit Account No. 50-1314. A copy of this paper is enclosed.

Respectfully submitted,

HOGAN & HARTSON L.L.P.

By:

William H. Wright

Registration No. 36,312

Attorney for Applicant(s)

500 South Grand Avenue, Suite 1900
Los Angeles, California 90071
Telephone: 213-337-6700
Facsimile: 213-337-6701

RECEIVED

MAY 12 2000

TECHNOLOGY CENTER 280